ABSTRACT OF THE DISCLOSURE

5

10

A magnetic memory of the present invention includes two or more memory layers and two or more tunnel layers that are stacked in the thickness direction of the layers. The two or more memory layers are connected electrically in series. A group of first layers includes at least one layer selected from the two or more memory layers. A group of second layers includes at least one layer selected from the two or more memory layers. A resistance change caused by magnetization reversal in the group of first layers differs from a resistance change caused by magnetization reversal in the group of second layers.